2SC1515(K)

Silicon NPN Triple Diffused

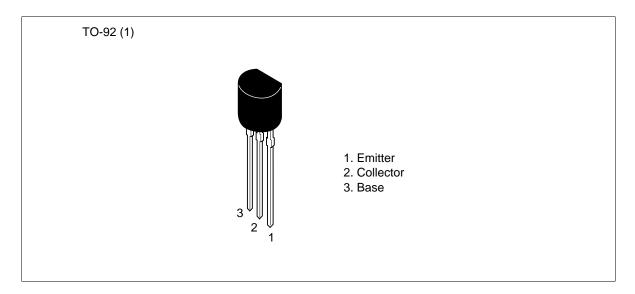
HITACHI

ADE-208-1055 (Z) 1st. Edition Mar. 2001

Application

High voltage switching

Outline





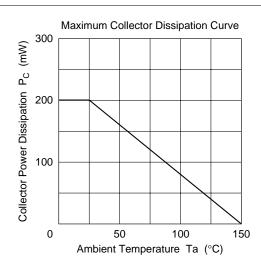
2SC1515 (K)

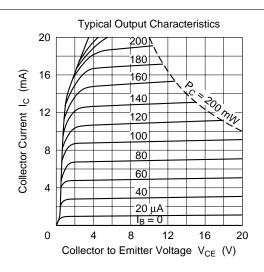
Absolute Maximum Ratings ($Ta = 25^{\circ}C$)

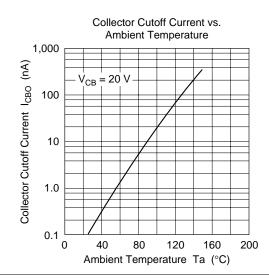
Item	Symbol	Ratings	Unit	
Collector to base voltage	V_{CBO}	200	V	
Collector to emitter voltage	V_{CES}	200	V	
	$V_{\sf CEO}$	150	V	
Emitter to base voltage	V_{EBO}	5	V	
Collector current	I _c	50	mA	
Collector power dissipation	P _c	200	mW	
Junction temperature	Tj	150	°C	
Storage temperature	Tstg	-55 to +150	°C	

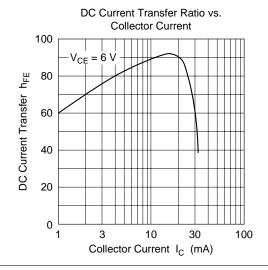
Electrical Characteristics ($Ta = 25^{\circ}C$)

Item	Symbol	Min	Тур	Max	Unit	Test conditions
Collector to emitter breakdown voltage	$V_{(BR)CES}$	200	_	_	V	$I_{c} = 10 \ \mu A, \ R_{BE} = 0$
	$V_{\text{(BR)CEO}}$	150		_	V	$I_{\rm C}$ = 1 mA, $R_{\rm BE}$ = ∞
Emitter to base breakdown voltage	$V_{(BR)EBO}$	5	_	_	V	$I_{E} = 10 \ \mu A, \ I_{C} = 0$
Collector cutoff current	I _{CBO}	_	_	0.1	μΑ	$V_{CB} = 20 \text{ V}, I_{E} = 0$
DC current transfer ratio	h _{FE}	30	_	300		$V_{CE} = 6 \text{ V}, I_{C} = 10 \text{ mA}$
Collector to emitter saturation voltage	$V_{\text{CE(sat)}}$	_	_	1.0	V	$I_{\rm C}$ = 10 mA, $I_{\rm B}$ = 1 mA
Base to emitter saturation voltage	$V_{\text{BE}(\text{sat})}$	_	_	1.5	V	$I_C = 10 \text{ mA}, I_B = 1 \text{ mA}$
Gain bandwidth product	f⊤	60	_	_	MHz	$V_{CE} = 6 \text{ V}, I_{C} = 10 \text{ mA}$
Collector output capacitance	Cob	_	_	10	pF	$V_{CB} = 6 \text{ V}, I_{E} = 0, f = 1 \text{ MHz}$

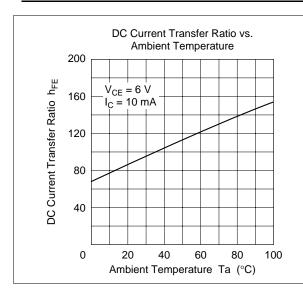


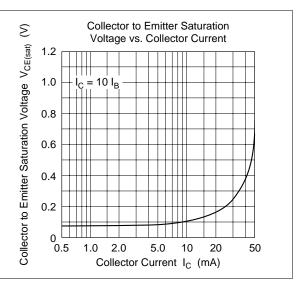




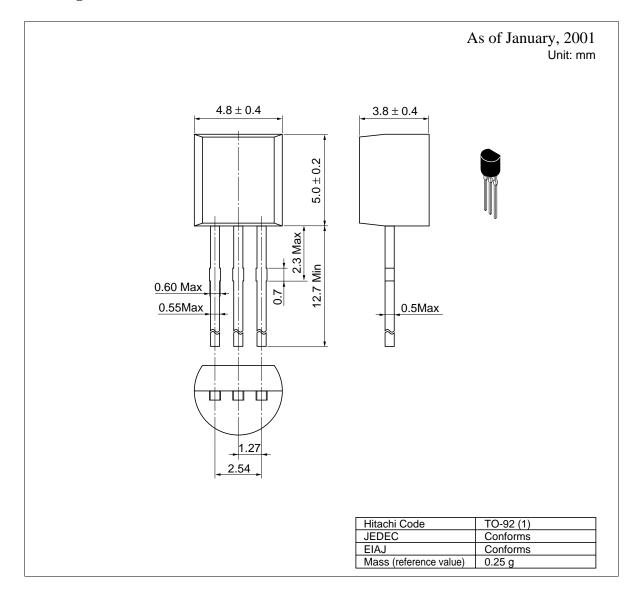


2SC1515 (K)





Package Dimensions



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